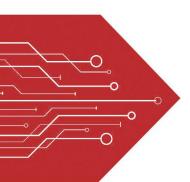
## MSKSEMI















**ESD** 

TVS

TSS

MOV

GDT

**PLED** 

# Broduct data sheet









### **SOT - 23**



- 1. BASE
- 2. EMITTER
- 3. COLLECTOR

#### **FEATURES**

• Complementary Type FMMT493

MARKING:593

#### MAXIMUM RATINGS (T<sub>a</sub>=25°C unless otherwise noted)

Symbol	Parameter	Value	Unit
V <sub>CBO</sub>	Collector-Base Voltage	-120	٧
V <sub>CEO</sub>	Collector-Emitter Voltage	-100	٧
V <sub>EBO</sub>	Emitter-Base Voltage	-5	V
Ic	Collector Current	-1	Α
Pc	Collector Power Dissipation	250	mW
R <sub>OJA</sub>	Thermal Resistance From Junction To Ambient	500	°C/W
T <sub>J</sub> ,T <sub>stg</sub>	Operation Junction and Storage Temperature Range	-55~+150	℃

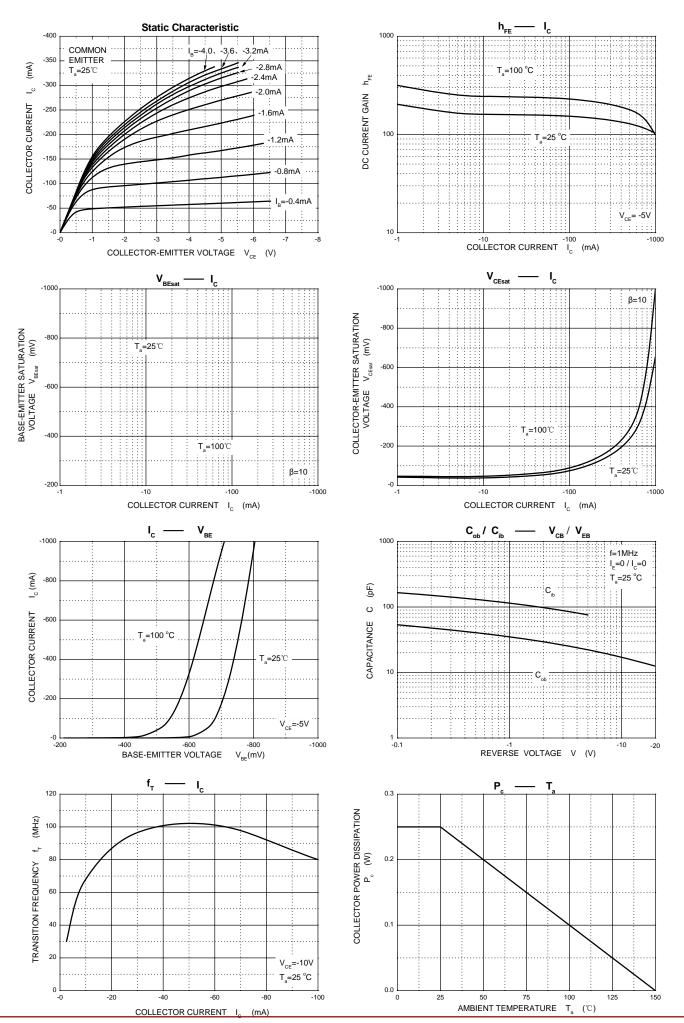
#### ELECTRICAL CHARACTERISTICS (T<sub>a</sub>=25°C unless otherwise specified)

Parameter	Symbol	Test conditions	Min	Тур	Max	Unit
Collector-base breakdown voltage	V <sub>(BR)CBO</sub>	I <sub>C</sub> =-100μA, I <sub>E</sub> =0	-120			V
Collector-emitter breakdown voltage	V <sub>(BR)CEO</sub>	I <sub>C</sub> =-10mA, I <sub>B</sub> =0	-100			V
Emitter-base breakdown voltage	V <sub>(BR)EBO</sub>	I <sub>E</sub> =-100μA, I <sub>C</sub> =0	-5			V
Collector cut-off current	I <sub>CBO</sub>	V <sub>CB</sub> =-100V, I <sub>E</sub> =0			-0.1	μA
Collector cut-off current	I <sub>CES</sub>	V <sub>CES</sub> =-100V, I <sub>E</sub> =0			-0.1	μA
Emitter cut-off current	I <sub>EBO</sub>	V <sub>EB</sub> =-4V, I <sub>C</sub> =0			-0.1	μA
	h <sub>FE(1)</sub> *	V <sub>CE</sub> =-5V, I <sub>C</sub> =-1mA	100			
DO comment again	h <sub>FE(2)</sub> *	V <sub>CE</sub> =-5V, I <sub>C</sub> =-250mA	100			
DC current gain	h <sub>FE(3)</sub> *	V <sub>CE</sub> =-5V, I <sub>C</sub> =-0.5A	100		300	
	h <sub>FE(4)</sub> *	V <sub>CE</sub> =-5V, I <sub>C</sub> =-1A	50			
Collector emitter acturation valtage	V <sub>CE(sat)1</sub> *	I <sub>C</sub> =-250mA, I <sub>B</sub> =-25mA			-0.2	V
Collector-emitter saturation voltage	V <sub>CE(sat)2</sub> *	I <sub>C</sub> =-500mA, I <sub>B</sub> =-50mA			-0.3	V
Base-emitter saturation voltage	V <sub>BE(sat)</sub> *	I <sub>C</sub> =-500mA, I <sub>B</sub> =-50mA			-1.1	V
Base-emitter voltage	V <sub>BE</sub> *	V <sub>CE</sub> =-5V, I <sub>C</sub> =-1mA			-1	V
Transition frequency	f <sub>T</sub>	V <sub>CE</sub> =-10V,I <sub>C</sub> =-50mA, f=100MHz	50			MHz
Collector output capacitance	C <sub>ob</sub>	V <sub>CB</sub> =-10V, I <sub>E</sub> =0, f=1MHz		5		pF

<sup>\*</sup>Pulse test: pulse width ≤300µs, duty cycle≤ 2.0%.

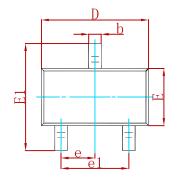
Semiconductor

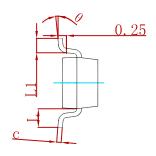


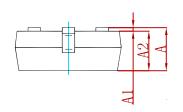




#### **PACKAGE MECHANICAL DATA**

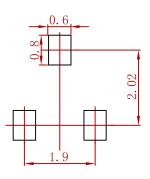






Symbol	Dimensions In Millimeters		Dimensions In Inches		
Symbol	Min	Max	Min	Max	
Α	0.900	1.150	0.035	0.045	
A1	0.000	0.100	0.000	0.004	
A2	0.900	1.050	0.035	0.041	
b	0.300	0.500	0.012	0.020	
С	0.080	0.150	0.003	0.006	
D	2.800	3.000	0.110	0.118	
Е	1.200	1.400	0.047	0.055	
E1	2.250	2.550	0.089	0.100	
е	0.950 TYP		0.037	7 TYP	
e1	1.800	2.000	0.071	0.079	
L	0.550 REF		0.022 REF		
L1	0.300	0.500	0.012	0.020	
θ	0°	8°	0°	8°	

### **Suggested Pad Layout**



- 1.Controlling dimension:in millimeters.2.General tolerance:± 0.05mm.3.The pad layout is for reference purposes only.

#### **REEL SPECIFICATION**

P/N	PKG	QTY
FMMT593	SOT-23	3000



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